

1.0 SCOPE

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die_Broc.pdf is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at www.analog.com/PM108

2.0 Part Number. The complete part number(s) of this specification follow:

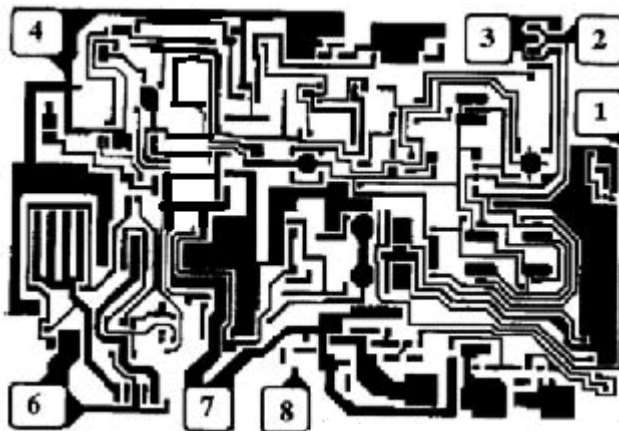
<u>Part Number</u>	<u>Description</u>
PM108-000C	Low-Input-Current Operational Amplifier
PM108R000C	Radiation tested Low-Input-Current Operational Amplifier

3.0 Die Information

3.1 Die Dimensions

Die Size	Die Thickness	Bond Pad Metalization
54 mil x 74 mil	19 mil \pm 2 mil	Al/Cu

3.2 Die Picture



1. COMP
2. -IN
3. +IN
4. V-
5. NC
6. OUT
7. V+
8. COMP

ASD0012750

Rev. I

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3.3 Absolute Maximum Ratings 1/

Supply Voltage (V_{CC}).....	± 22 V
Input Voltage (V_{IN}) 2/.....	± 15 V
Differential Input Current 3/.....	± 10 mA
Output Short-Circuit Duration.....	Indefinite
Storage Temperature Range	-65 °C to $+150$ °C
Junction Temperature (T_J).....	$+175$ °C
Ambient Temperature Range	-55 °C to $+125$ °C

Absolute Maximum Ratings Notes:

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- 2/ For supply voltages less than ± 15 V, the absolute maximum input voltage is equal to the supply voltage.
- 3/ The inputs are shunted with back-to-back diodes for overvoltage protection. Therefore, if a differential input voltage in excess of 1 V is applied between the inputs, excessive current will flow, unless some limiting resistance is provided.

4.0 Die Qualification

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.
 (a) Qual Sample Size and Qual Acceptance Criteria – 10/0
 (b) Qual Sample Package – DIP
 (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

Table I Notes:

Table I - Dice Electrical Characteristics					
Parameter	Symbol	Conditions 1/	Limit Min	Limit Max	Units
Input Offset Voltage	V_{IO}		-0.5	0.5	mV
Input Offset Current	I_{IO}		-0.2	0.2	nA
Input Bias Current	$\pm I_{IB}$		-0.1	2	nA
Power Supply Rejection Ratio	+PSRR	$+V_{CC} = +10$ V to $+20$ V, $-V_{CC} = -20$ V	-16	16	μ V/V
	-PSRR	$+V_{CC} = +20$ V, $-V_{CC} = -10$ V to -20 V	-16	16	
Input Voltage Range	IVR		± 15		V
Input Voltage Common Mode Rejection	CMR	$V_{CM} = IVR$	96		dB
Supply Current	I_{CC}	$\pm V_{CC} = \pm 15$ V		0.6	mA
Output Voltage Swing	$\pm V_{OP}$	$\pm V_{CC} = \pm 20$ V, $R_L = 10$ k Ω	± 16		V
Open Loop Voltage Gain	A_{VS}	$\pm V_{CC} = \pm 15$ V, $R_L = 10$ k Ω $V_{OUT} = \pm 10$ V	80		V/mV

Table I Notes:

1/ $V_{CC} = \pm 20$ V, $R_S = 50$ Ω , $V_{CM} = 0$ V, and $T_A = 25$ °C, unless otherwise specified.

Table II - Electrical Characteristics for Qual Samples

Parameter	Symbol	Conditions 1/3/	Sub- groups	Limit Min	Limit Max	Units
Input Offset Voltage 3/	V_{IO}		1	-0.5	0.5	mV
			2,3	-1	1	
			M, D, L, R	1	-2	
Input Offset Current 3/	I_{IO}		1	-0.2	0.2	nA
			2,3	-0.4	0.4	
			M, D, L, R	1	-1	
Input Bias Current 3/	$\pm I_{IB}$		1	-0.1	2	
			2,3	-0.4	0.4	
			M, D, L, R	1	-25	
Input Offset Voltage Temperature Sensitivity 2/	$\Delta V_{IO} / \Delta T$		2,3	-5	5	$\mu V/^{\circ}C$
Open Loop Voltage Gain 3/	V_{VS}	$\pm V_{CC} = \pm 15 V, R_L = 10 K\Omega,$ $V_{OUT} = \pm 10 V$	4	80		V/mV
			5,6	40		
			M, D, L, R	4	10	
Power Supply Rejection Ratio 2/	+PSRR	$+V_{CC} = +10 V$ to $+20 V$ $-V_{CC} = -20 V$	1, 2, 3	-16	16	$\mu V/V$
	-PSRR	$+V_{CC} = +20 V$ $-V_{CC} = -10 V$ to $-20 V$	1, 2, 3	-16	16	
Input Voltage Range 2/	IVR		1, 2, 3	± 15		V
Supply Current 2/	I_{CC}	$V_{CC} = \pm 15 V$	1, 2		0.6	mA
			3		0.8	
Input Voltage Common Mode Rejection Ratio 2/	CMRR	$V_{CM} = IVR$	1, 2, 3	96		dB
Output Short-Circuit Current 2/	$I_{OS(+)}$	$\pm V_{CC} = \pm 15 V, t \leq 25 mS$	1	-15	15	mA
	$I_{OS(-)}$					
Output Voltage Swing 2/	$\pm V_{OP}$	$\pm V_{CC} = \pm 20 V, R_L = 10 K\Omega$	4, 5, 6	± 16		V

Table II Notes:

1/ $V_{CC} = \pm 20 V, R_S = 50 \Omega,$ and $V_{CM} = 0 V,$ unless otherwise specified.

2/ Not tested post-irradiation

3/ Irradiated at dose rate = 50 - 300 rads (Si)/s in accordance with MIL-STD-883, method 1019, condition A, and is guaranteed to a maximum total dose specified of 100 krad (Si). The effective dose rate after extended room temperature anneal = 1.15 rad (Si)/s per MIL-STD-883, method 1019, condition A, section 3.11.2. The total dose specification for this device only applies to the specified effective dose rate, or lower, environment.

Table III - Life Test Endpoint and Delta Parameter
 (Product is tested in accordance with Table II with the following exceptions)

Parameter	Symbol	Sub-groups	Post Burn-in Limit		Post Life Test Limit		Life Test Delta	Units
			Min	Max	Min	Max		
Input Offset Voltage	V _{IO}	1		±0.75		±1	±0.25	mV
		2, 3				±1.5		
Input Bias Current	±I _B	1	-0.1	2.5	-0.1	±3	±0.5	nA
		2			-1	±3		
		3			-0.1	±4		
Input Offset Current	I _{IO}	1		±0.3		±0.3		nA
		2, 3				±0.5		

5.0 Life Test/Burn-In Information

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B or C.
- 5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
A	Initiate	7-Feb-02
B	Add radiation test limits. Update web address.	9-Jan-03
C	Make correction file names (see OP215)	9-Jan-03
D	Update 1.0 Scope description.	09-Jul-07
E	Update header/footer & add to 1.0 scope description.	19-Feb-08
F	Add Junction Temperature(T _J).....175°C to 3.3 Absolute Maximum Ratings	March 31, 2008
G	Updated Section 4.0c note to indicate pre-screen temp testing being performed.	6-JUN-2009
H	Update fonts and sizes to ADI standard	3-Oct-2011
I	Add dose rate environment at Table II Notes.	08-Jun-21